

39/428/10

Abstract of the disclosure

A ferroelectric random access memory (FeRAM) device,  
includes: a plurality of memory cells arranged in an  $M \times J$  matrix,  
5 wherein  $M$  is a positive integer more than three and  $J$  is a positive  
integer; a number of reference cells connected to each column of  
the memory cells; and a cell selection means for selecting a memory  
cell in response to address signals from an external circuit and  
selecting a reference cell corresponding to the selected memory  
10 cell.

0042840 402200